

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
04 September 2025 (04.09.2025)



(10) International Publication Number
WO 2025/183741 A2

(51) International Patent Classification:
Not classified

(21) International Application Number:
PCT/US2024/048270

(22) International Filing Date:
25 September 2024 (25.09.2024)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
18/477,058 28 September 2023 (28.09.2023) US

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE,

(54) Title: HIGH DYNAMIC RANGE TRACK AND HOLD AMPLIFIER OUTPUT STAGE USING LOW VOLTAGE DEVICES

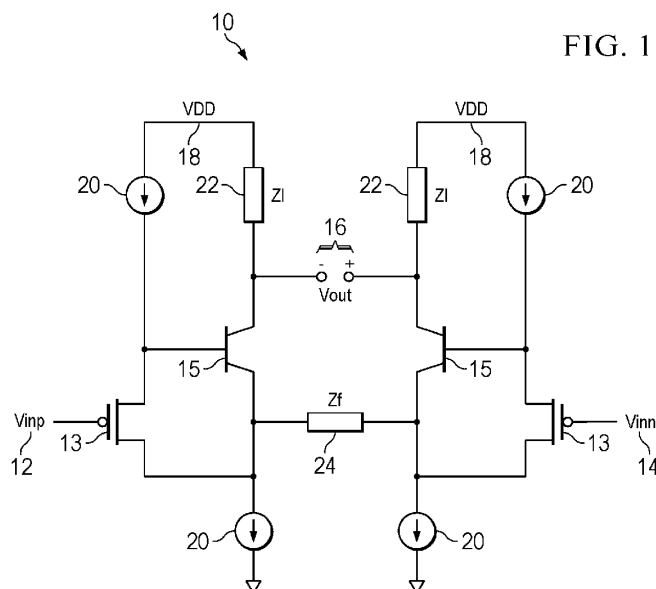


FIG. 1

(57) Abstract: A sample and hold amplifier output buffer with the low leakage of metal oxide semiconductor field effect transistors (MOSFET) combined with the linearity and dynamic range of silicon-germanium (SiGe) bipolar junction transistors (BJT). In one aspect, the present disclosure provides a sample and hold amplifier output buffer placing a MOSFET input device between the base and emitter of a high linearity SiGe BJT.

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WO 2025/183741 A2

SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

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